## N-Channel 80-V (D-S) MOSFET

## **Key Features:**

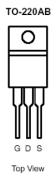
- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- · Fast switching speed

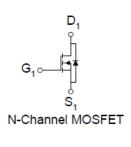
<b>Typical</b>	Applications	
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
80	11 @ V <sub>GS</sub> = 10V	90 <sup>a</sup>		
	13 @ V <sub>GS</sub> = 4.5V	90"		







ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter			Limit	Units			
Drain-Source Voltage			80	V			
Gate-Source Voltage	$V_{GS}$	±20	V				
Continuous Drain Current a	T <sub>A</sub> =25°C	$I_D$	90a				
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	350	Α				
Continuous Source Current (Diode Conduction) a	I <sub>S</sub>	120					
Power Dissipation <sup>a</sup>	T <sub>A</sub> =25°C	$P_{D}$	300	W			
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to 175	°C			

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 10 sec	$R_{\theta JA}$	62.5	°C/W		
Maximum Sunction-to-Ambient	Steady State	IΛθΊΑ	0.5	C/VV		

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#### Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature

### **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	1			V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA	
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA
On-State Drain Current	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	45			Α
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			11	mΩ
Diain-Source On-Resistance	r <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			13	11152
Forward Transconductance	g <sub>fs</sub>	$V_{DS} = 15 \text{ V}, I_{D} = 45 \text{ A}$		40		S
Diode Forward Voltage	$V_{SD}$	$I_{S} = 60 \text{ A}, V_{GS} = 0 \text{ V}$		0.9		V
		Dynamic				
Total Gate Charge	$Q_g$			58		
Gate-Source Charge	$Q_gs$	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		14		nC
Gate-Drain Charge	$Q_gd$			39		
Turn-On Delay Time	t <sub>d(on)</sub>			19		
Rise Time	t <sub>r</sub>	$V_{DS}$ = 40 V, $R_L$ = 2 $\Omega$ , $I_D$ = 20 A,		45		ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		178		115
Fall Time	t <sub>f</sub>			62		
Input Capacitance	C <sub>iss</sub>			4021		
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		449		pF
Reverse Transfer Capacitance	$C_{rss}$			440		

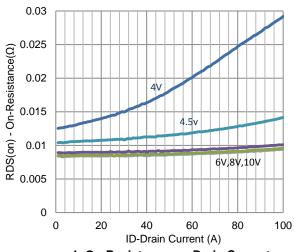
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

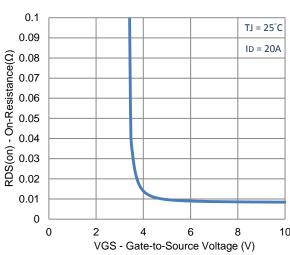
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### **Typical Electrical Characteristics**

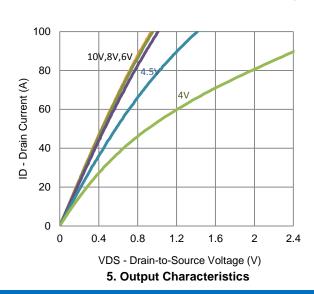
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1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



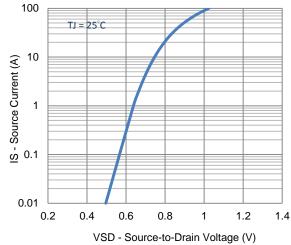
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TJ = 25°C

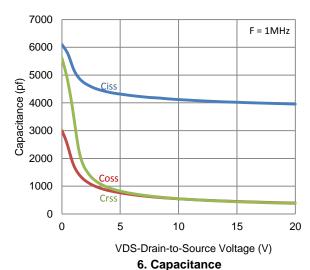
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(V) the bound of the control of

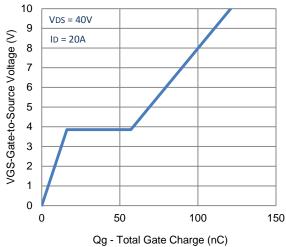
2. Transfer Characteristics



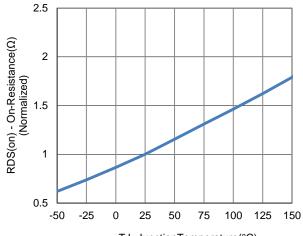
4. Drain-to-Source Forward Voltage



### **Typical Electrical Characteristics**

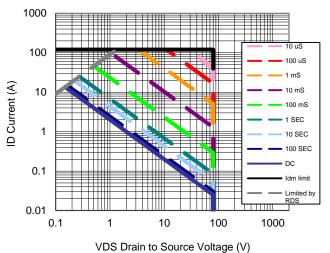




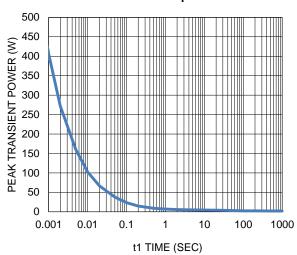


TJ -JunctionTemperature(°C)

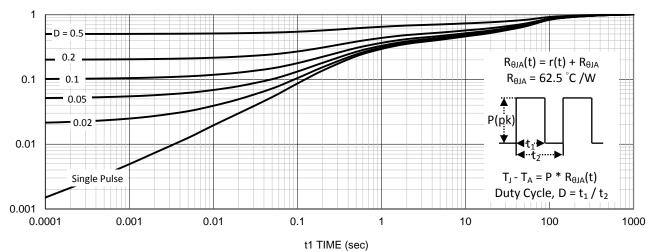




9. Safe Operating Area

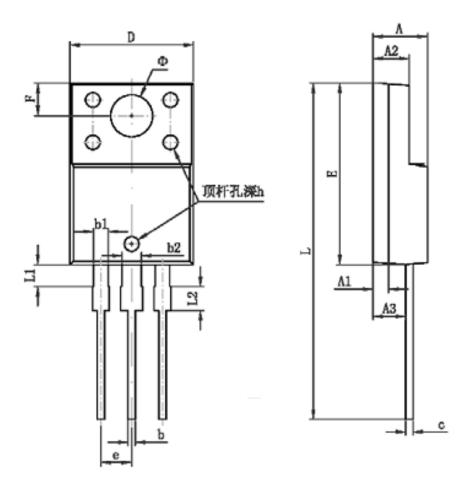


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

# **Package Information**



Cumbal	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min	Max	Min	Max		
A	4.300	4.700	0.169	0.185		
A1	1.300	1.300 REF		REF		
A2	2.800	3.200	0.110	0.126		
A3	2.500	2.900	0.098	0.114		
b	0.500	0.750	0.020	0.030		
b1	1.100	1.350	0.043	0.053		
b2	1.500	1.750	0.059	0.069		
С	0.500	0.750	0.020	0.030		
D	9.960	10.360	0.392	0.408		
E	14.800	15.200	0.583	0.598		
e	2.540	0 TYP 0.100 TYP		2.540 TYP		) TYP
F	2.700	0 REF 0.106 REF		REF		
Ф	3.500	0.138 REF		REF		
h	0.000	0.300	0.000	0.012		
L	28.000	28.400	1.102	1.118		
L1	1.700	1.900	0.067	0.075		
L2	1.900	2.100	0.075	0.083		